

	Type	L #	Hits	Search Text	DBs	Comments
1	BRS	L1	271357	257/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	
2	BRS	L2	89143	1 and (transistor or MOS or MOFET? or (metal near oxide near transistor))	USPAT; US-PGPUB; EPO; JPO; DERWENT	
3	BRS	L3	1458	2 and (SiGe or Si-Ge or (silicon near germanium)) near (channel or layer or film)	USPAT; US-PGPUB; EPO; JPO; DERWENT	
4	BRS	L4	70	3 and (silicon near cap)	USPAT; US-PGPUB; EPO; JPO; DERWENT	
5	BRS	L5	2	4 and (free near germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT	
6	BRS	L6	42	ma-yanjun.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT	
7	BRS	L7	0	6 and (free near germanium) near dielectric	USPAT; US-PGPUB; EPO; JPO; DERWENT	
8	BRS	L8	2	6 and (free near germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT	
9	BRS	L9	65	((SiGe or Si-Ge or (silicon near germanium)) near (channel or MOS or MOSFET or transistor)).ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT	
10	BRS	L10	0	9 and (free near germanium) near dielectric	USPAT; US-PGPUB; EPO; JPO; DERWENT	
11	BRS	L11	8	9 and (silicon near cap)	USPAT; US-PGPUB; EPO; JPO; DERWENT	
12	BRS	L12	609339	(transistor or MOS or MOFET? or (metal near oxide near transistor))	USPAT; US-PGPUB; EPO; JPO; DERWENT	
13	BRS	L13	2302	12 and (SiGe or Si-Ge or silicon-germanium or (silicon near germanium)) near (channel or layer or film)	USPAT; US-PGPUB; EPO; JPO; DERWENT	
14	BRS	L14	99	13 and (silicon near cap)	USPAT; US-PGPUB; EPO; JPO; DERWENT	
15	BRS	L15	0	14 and (free near germanium) near (gate near dielectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT	
16	BRS	L16	4	14 and dummy near gate	USPAT; US-PGPUB; EPO; JPO; DERWENT	